

ECH8315

Power MOSFET –30V, 25mΩ, –7.5A, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to low on resistance. This device is suitable for applications with low on resistance requirements.

Features

- Low On-Resistance
- 4V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

- Load Switch
- Protection Switch for Lithium-ion Battery
- Motor Driver

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	–30	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	–7.5	A
Drain Current (Pulse) PW ≤ 10μs, duty cycle ≤ 1%	IDP	–40	A
Power Dissipation When mounted on ceramic substrate (900mm ² × 0.8mm)	PD	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² × 0.8mm)	RθJA	83.3	°C/W

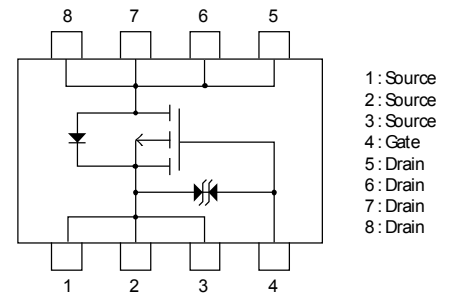


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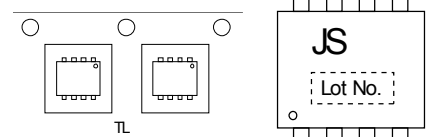
VDSS	RDS(on) Max	ID Max
–30V	25mΩ@ –10V	–7.5A
	44mΩ@ –4.5V	
	49mΩ@ –4V	

ELECTRICAL CONNECTION P-Channel



PACKING TYPE : TL

MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

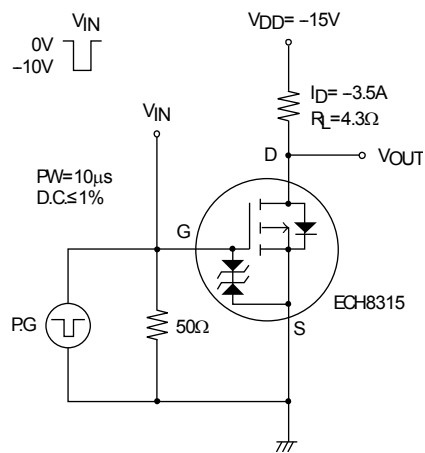
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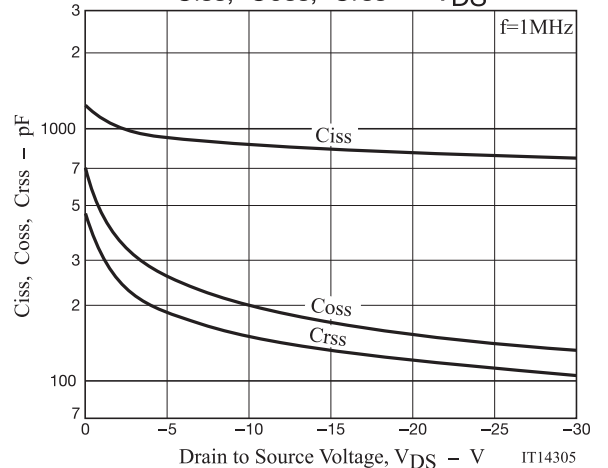
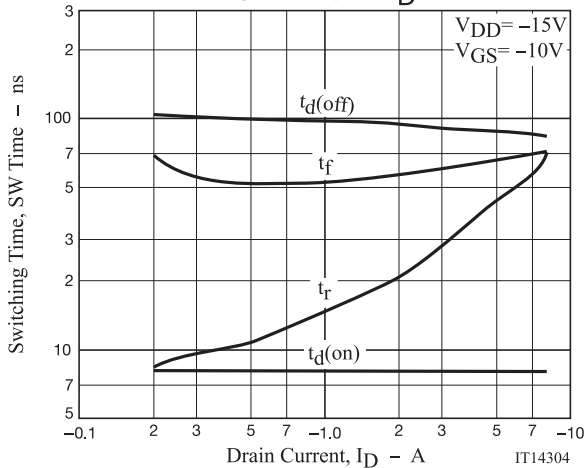
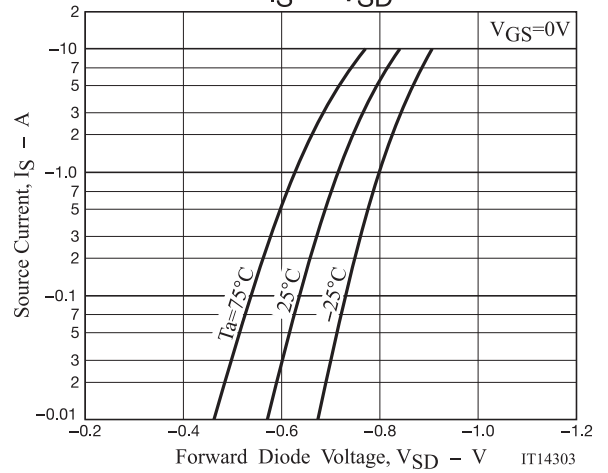
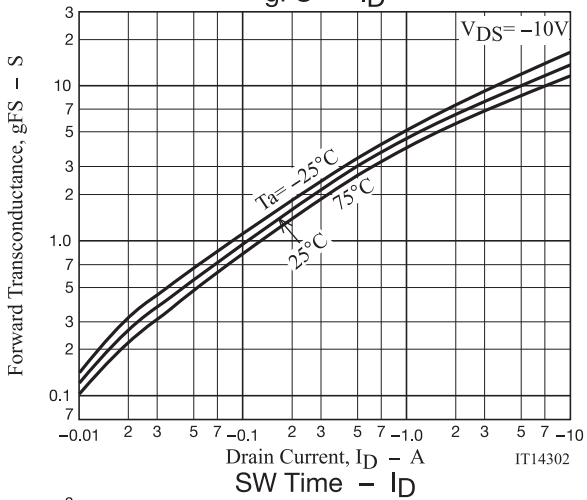
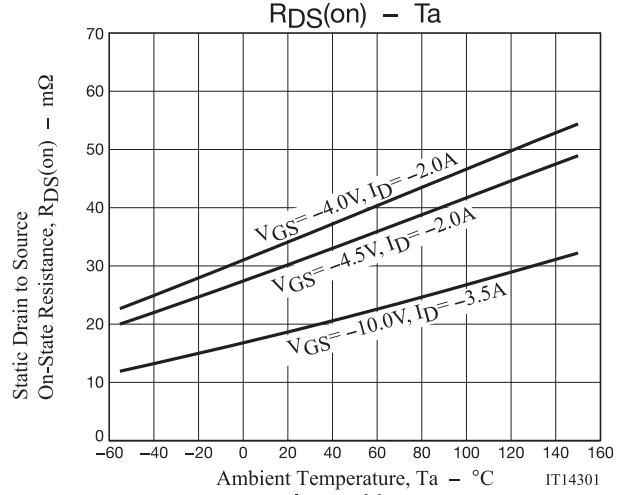
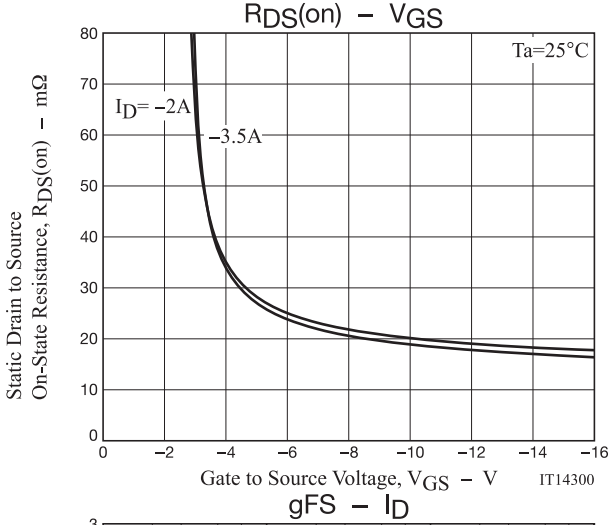
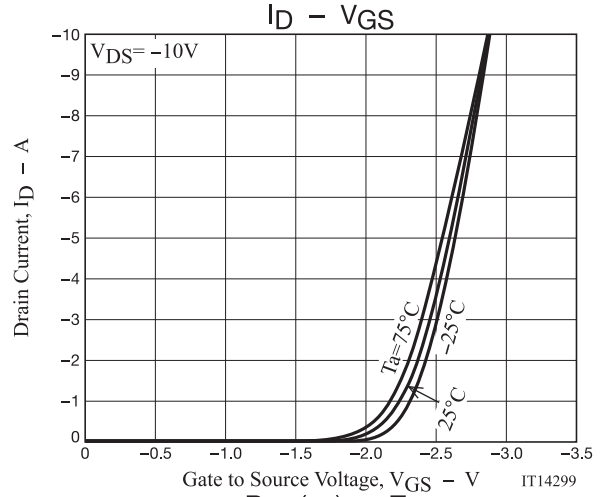
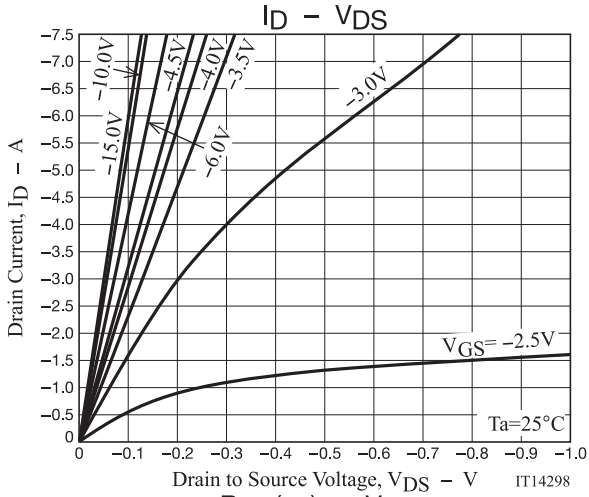
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-3.5A	5	8.4		S
Static Drain to Source On-State Resistance	R _{DS(on)1}	I _D =-3.5A, V _{GS} =-10V		19	25	mΩ
	R _{DS(on)2}	I _D =-2A, V _{GS} =-4.5V		31	44	mΩ
	R _{DS(on)3}	I _D =-2A, V _{GS} =-4V		35	49	mΩ
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		875		pF
Output Capacitance	C _{oss}			200		pF
Reverse Transfer Capacitance	C _{rss}			150		pF
Turn-ON Delay Time	t _{d(on)}		See specified Test Circuit		8.1	
Rise Time	t _r			33		ns
Turn-OFF Delay Time	t _{d(off)}			92		ns
Fall Time	t _f			60		ns
Total Gate Charge	Q _g	V _{DS} =-15V, V _{GS} =-10V, I _D =-7.5A			18	
Gate to Source Charge	Q _{gs}			2.1		nC
Gate to Drain "Miller" Charge	Q _{gd}			4.7		nC
Forward Diode Voltage	V _{SD}		I _S =-7.5A, V _{GS} =0V		-0.82	-1.2

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit





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